

S/N Unknown

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Jerome M. Eldridge et al. Examiner: Unknown
Serial No.: Unknown Group Art Unit: Unknown
Filed: Herewith Docket: 1303.063US2
Title: GRADED COMPOSITION METAL OXIDE TUNNEL BARRIER INTERPOLY
INSULATORS

COMMUNICATION CONCERNING RELATED APPLICATIONS

*Noted, DJ
June 2004*
Mail Stop Patent Application
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Applicants would like to bring to the Examiner's attention the following related applications in the above-identified patent application:

<u>Serial/Patent No.</u>	<u>Filing Date</u>	<u>Attorney Docket</u>	<u>Title</u>
09/945507	August 30, 2001	1303.014US1	FLASH MEMORY WITH LOW TUNNEL BARRIER INTERPOLY INSULATORS
09/945395	August 30, 2001	1303.019US1	DRAM CELLS WITH REPRESSED FLOATING GATE MEMORY, LOW TUNNEL BARRIER INTERPOLY INSULATORS
09/945498	August 30, 2001	1303.024US1	INTEGRATED CIRCUIT MEMORY DEVICE AND METHOD
09/945512	August 30, 2001	1303.027US1	IN SERVICE PROGRAMMABLE LOGIC ARRAYS WITH LOW TUNNEL BARRIER INTERPOLY INSULATORS
09/945554	August 30, 2001	1303.028US1	SRAM CELLS WITH REPRESSED FLOATING GATE MEMORY, LOW TUNNEL BARRIER INTERPOLY INSULATORS

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Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)	Complete if Known	
	Applicant Number	Unknown 10/781,035
	Filing Date	Even Date Herewith
	First Named Inventor	Eldridge, Jerome
	Group Art Unit	Unknown 2818
	Examiner Name	Unknown
Sheet 1 of 6		Attorney Docket No: 1303.063US2

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First Named Inventor	Eldridge, Jerome
Group Art Unit	Unknown
Examiner Name	Unknown

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OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS

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**INFORMATION DISCLOSURE
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Application Number Unknown

Filing Date Even Date Herewith

First Named Inventor Eldridge, Jerome

Group Art Unit Unknown

Examiner Name Unknown

Sheet 3 of 6

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	Application Number	Unknown
	Filing Date	Even Date Herewith
	First Named Inventor	Eldridge, Jerome
	Group Art Unit	Unknown
	Examiner Name	Unknown
Sheet 4 of 6		Attorney Docket No: 1303.063US2

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Sheet 5 of 6

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OTHER DOCUMENTS – NON PATENT LITERATURE DOCUMENTS

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